

IN THE SPECIFICATION

Please replace the paragraph on page 6, starting at line 17 with the following:

In an anisotropical etching process, with respect to the lower electrode layer, a photoresist pattern and the lower electrode layer typically have a low etch selectivity. This can result in a difficulty wherein a polymer is produced that may result in a slope-etching tendency. The hard mask layer is used to prevent this problem and to form a vertical sidewall. A damascene process can be used to form the lower electrode. Thus, a sacrificial oxide layer 150, as shown in FIG. 11, is formed on the interlayer dielectric layer[,]12, a node hole 152 is formed at a region where the lower electrode will be formed, and a lower electrode material fills the node hole by using an electroplate method. The hard mask layer may be a single layer or a multiple layer including at least one selected from a group of silicon oxide, titanium nitride, titanium, titanium oxide and BST. A photoresist pattern (not shown) is formed on the hard mask layer and is used as an etch mask to form a hard mask pattern 137 covering a lower electrode region. The photoresist pattern is removed by ashing. The lower electrode layer is etched by using the hard mask pattern 137 as an etch mask to form a lower electrode 135 of a cylindrical shape. Then, the hard mask pattern 137 may be removed.